

Super
Nemo
Absolute
Time
Stamper

**A high resolution and large dynamic
range time stamper chip**

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Context

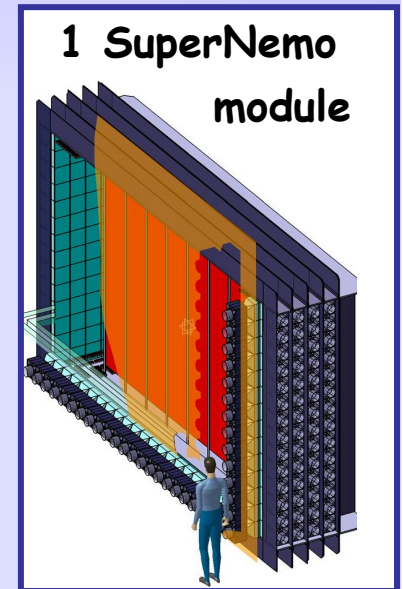
Aim : investigation of neutrinoless double-beta decay
To answers to questions on the nature of the neutrino.

The SuperNemo detector :

20 modules composed of tracker to identify the particle path
and a calorimeter to measure the particle energy

Requirements for the Calorimeter Front-End Electronics

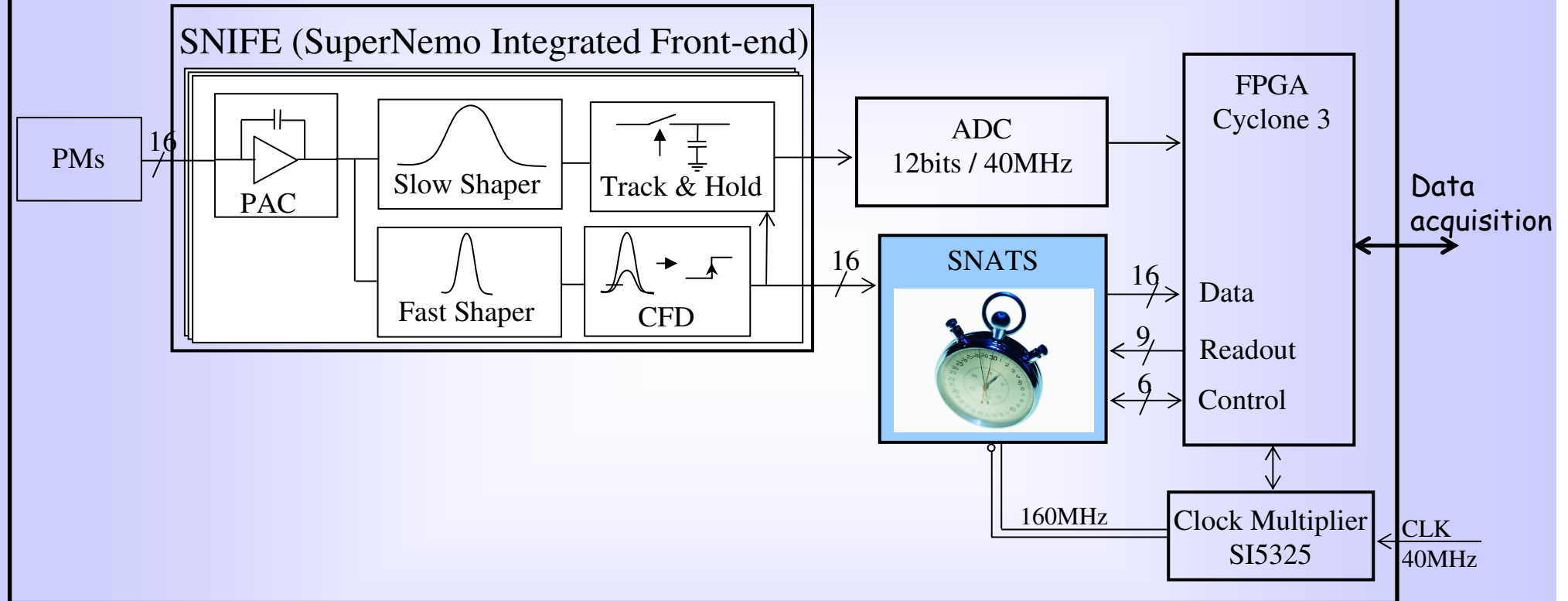
To work without a hardware trigger and with absolute time
measurements providing a time resolution about 100 ps RMS



SNATS: Super Nemo Absolute Time Stamper

a high performance TDC chip with
a high resolution of 70ps RMS and large dynamic range of 53 bits

16 channels front-end board



20000 photomultipliers $\Rightarrow$ 1250 SNATS chips

AMS CMOS 0.35 μ m Technology (C35B4)

Clock frequency : 160MHz

32 cells DLL

} delay cell $\approx$ 195ps

DNL <10%

Range : 53 bits

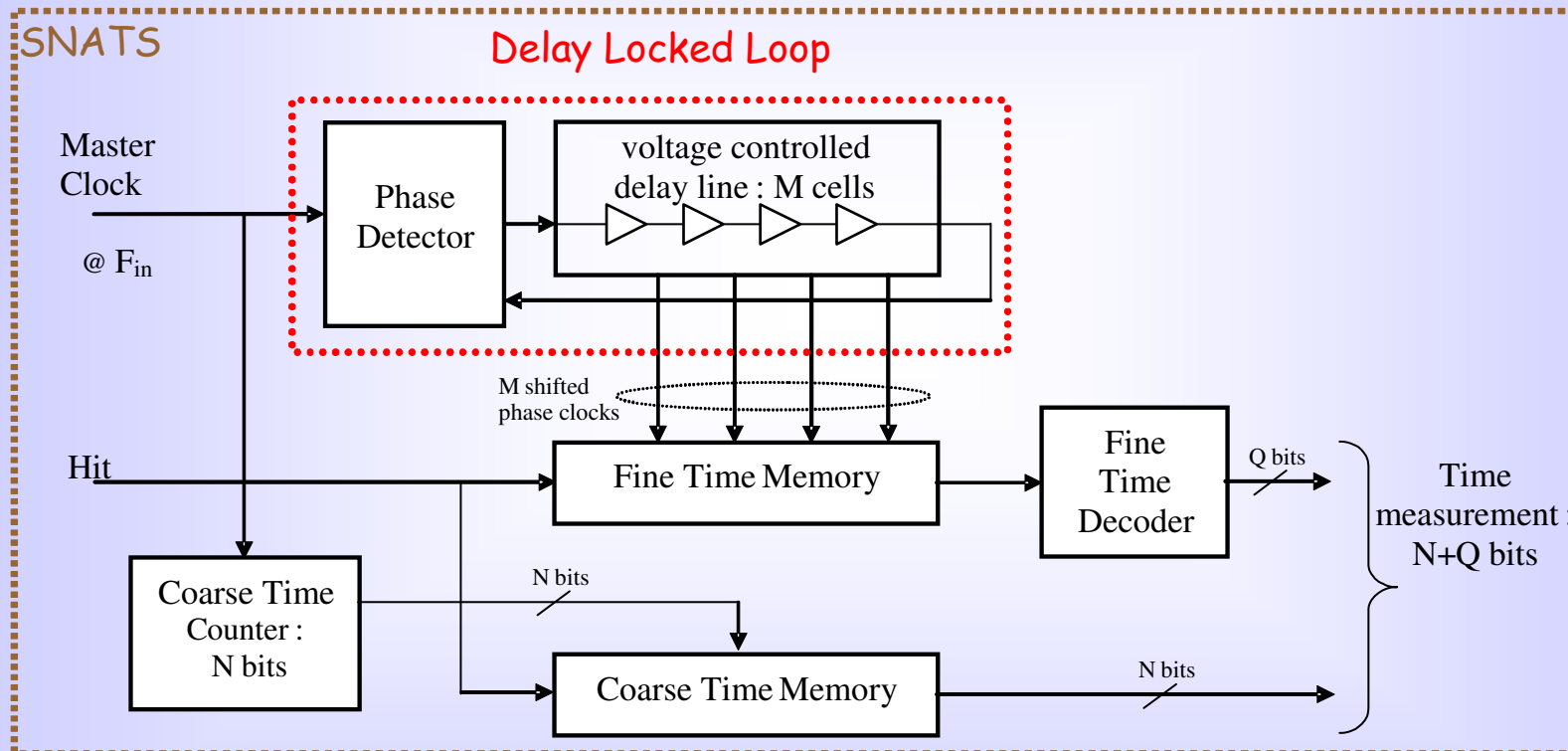
↳ 48-bit gray counter ($\approx$ 20 days)

↳ 5-bit gray encoder for status of DLL

↳ 16-bit parallel data output (4 words of 16 bits)

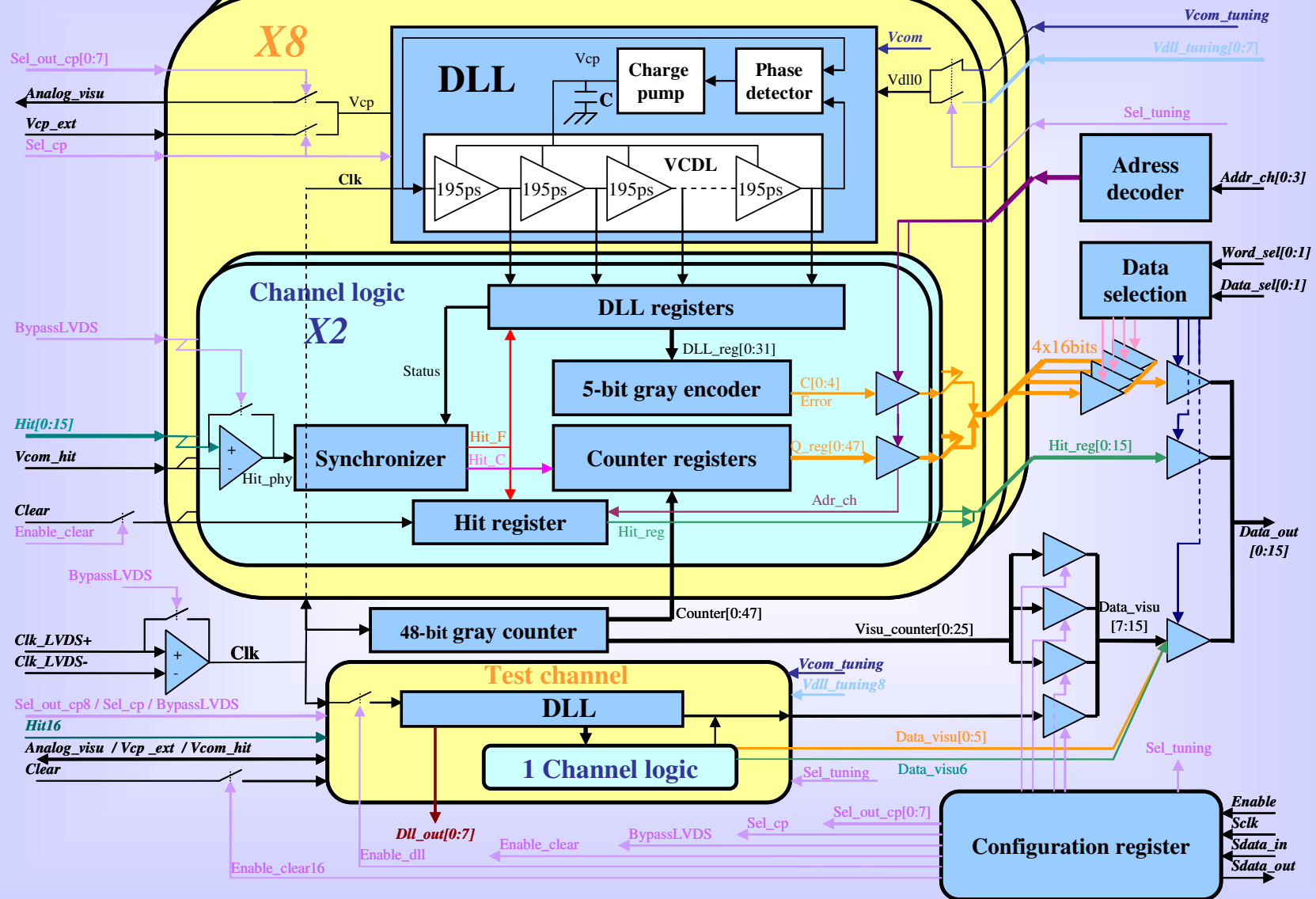
16 channels/chip

One fine time measurement (High resolution) $\Rightarrow$ DLL
 One coarse time measurement (range) $\Rightarrow$ N-bit counter

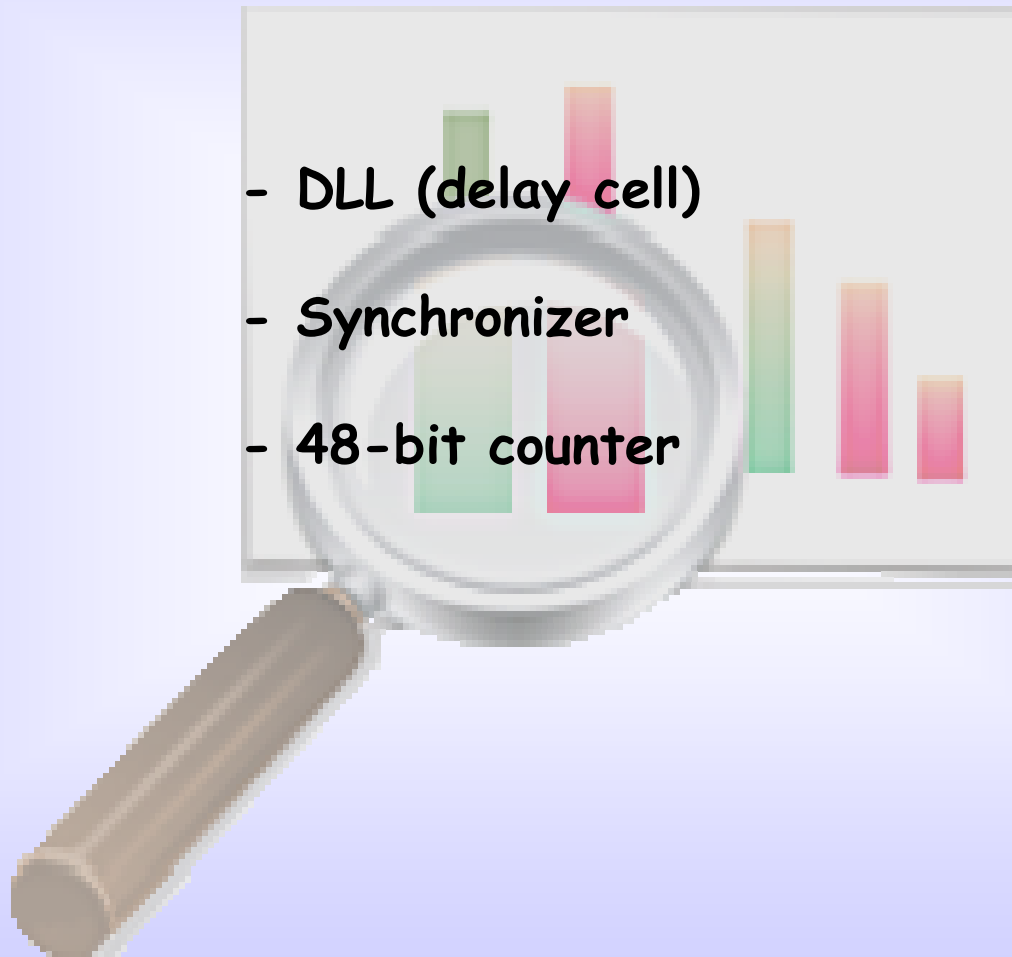


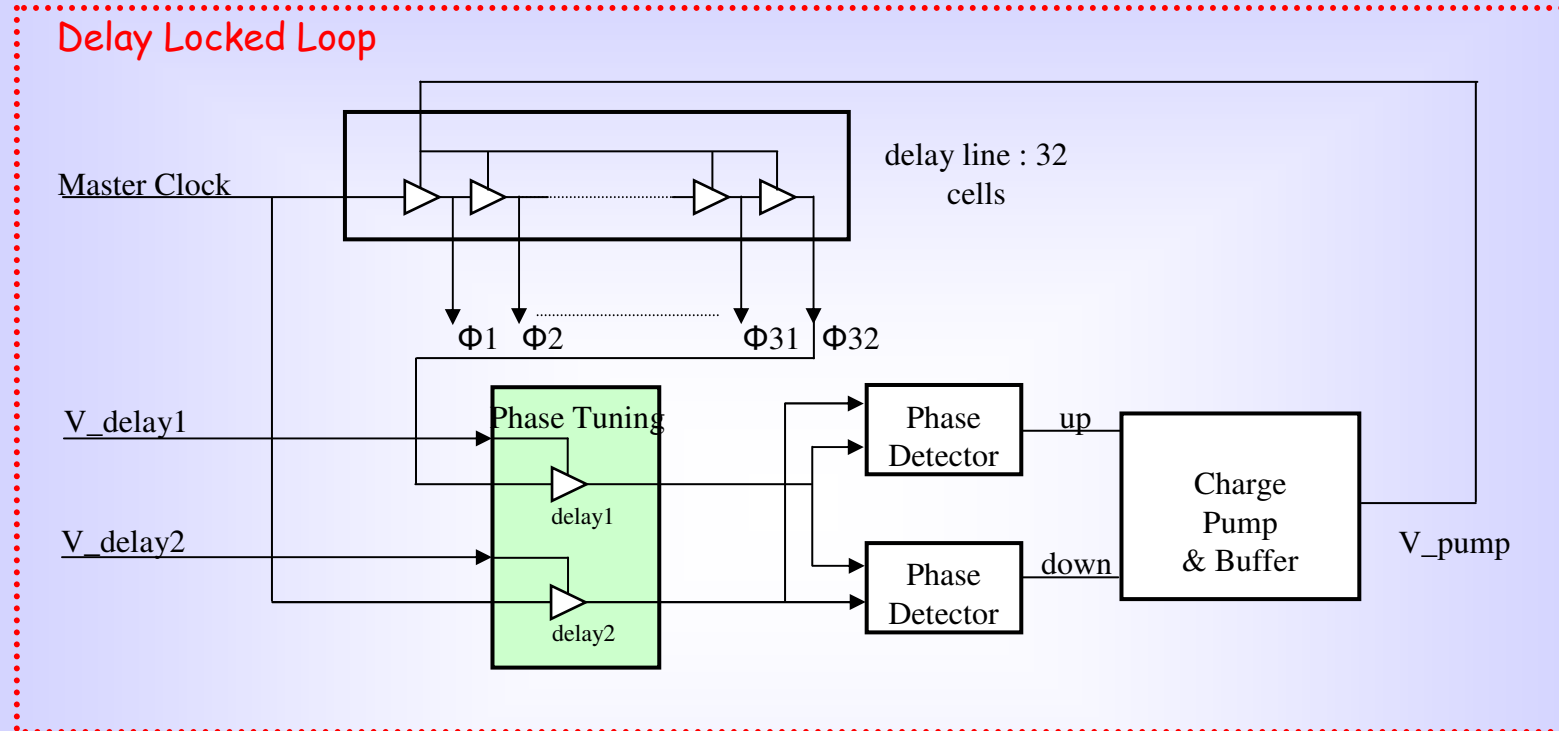
SNATS : architecture

8 blocks
16 channels



- DLL (delay cell)
- Synchronizer
- 48-bit counter

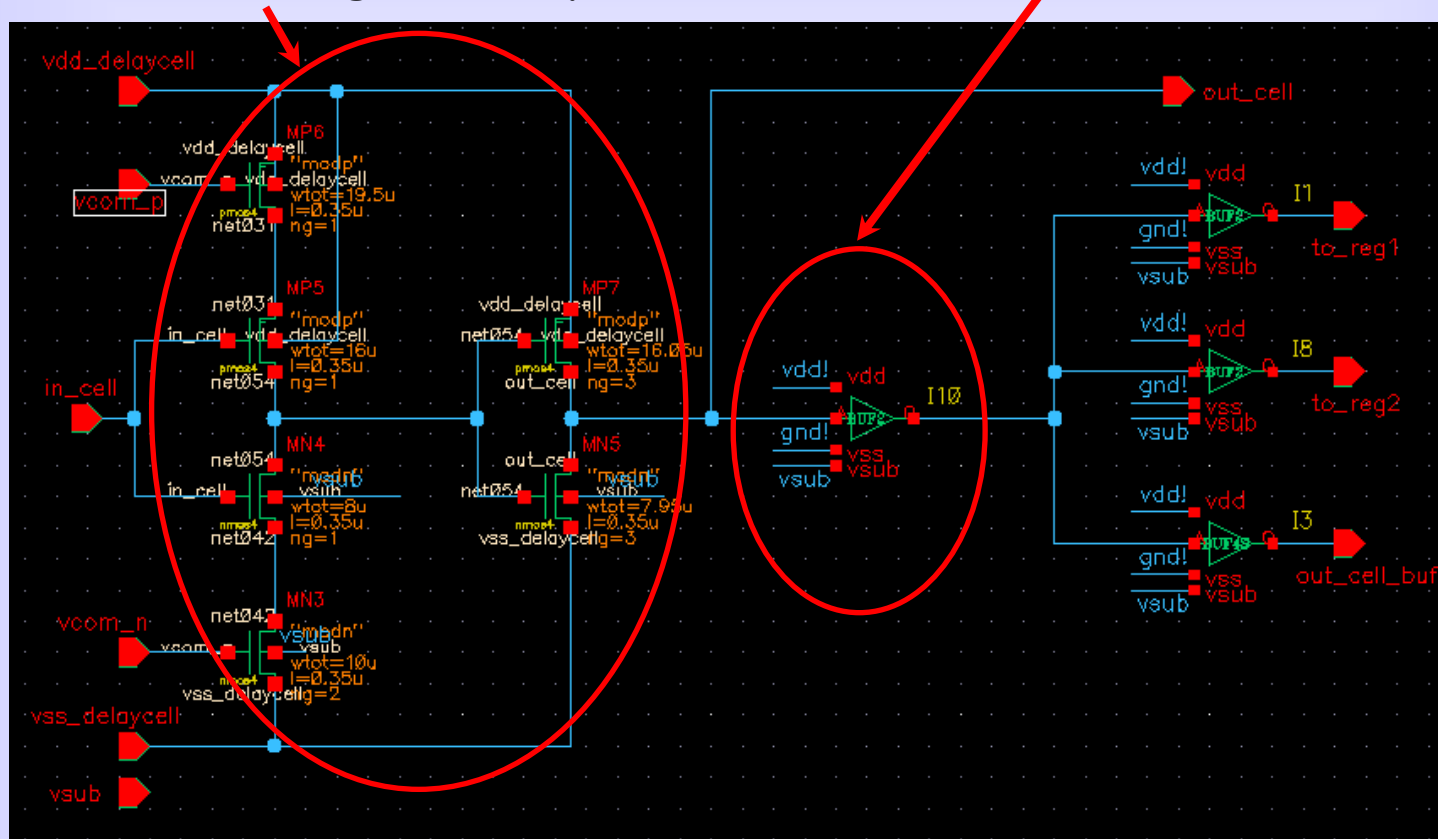




➡ Phase error < 20ps

A starved inverter followed by a standard inverter : gain $\approx 30\text{ps}$

1 buffer : gain $\approx 30\text{ps}$



nominal delay $\approx 195\text{ps}$ with a 30ps margin

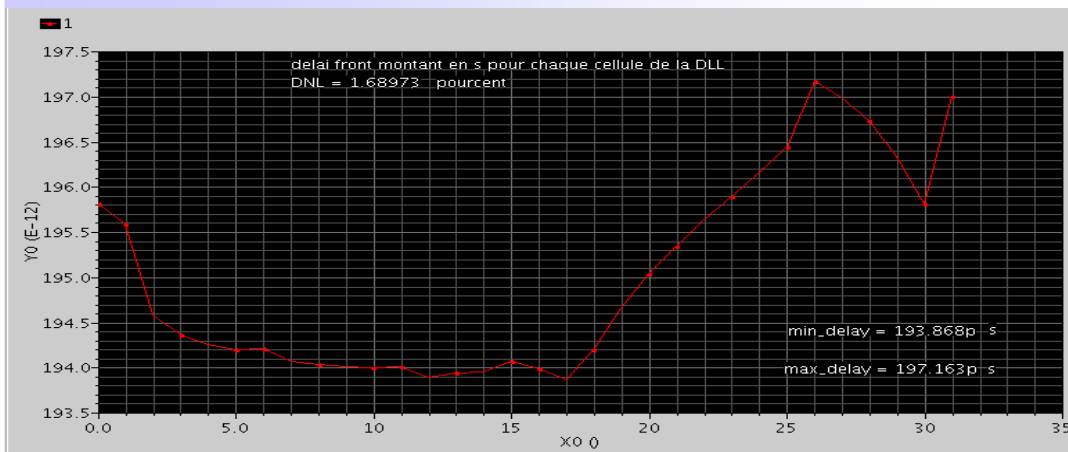


SNATS : post layout simulations (typical parameters)

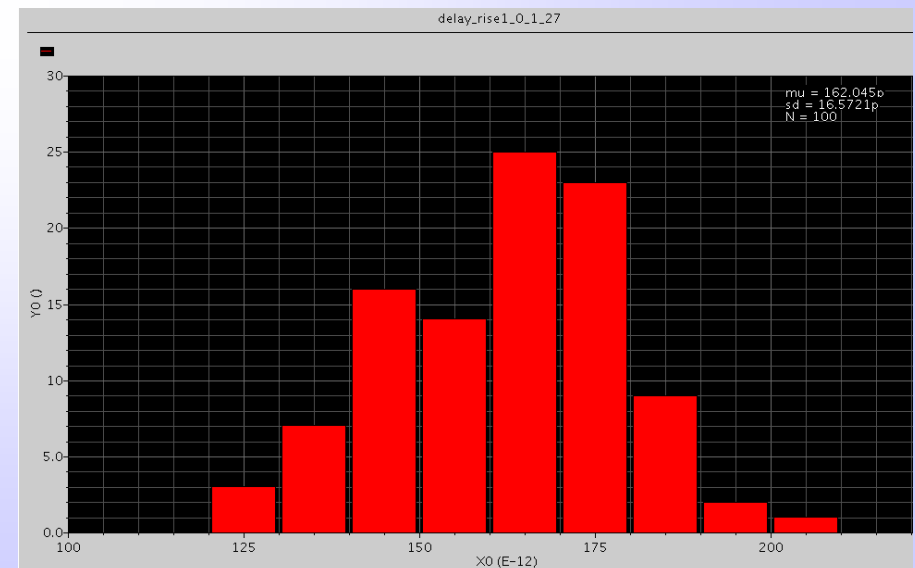
Slope of delay cell $\approx 0.15\text{ps/mV}$

Minimum delay $\approx 150\text{ps}$ at 27°C
 $\approx 166\text{ps}$ at 60°C

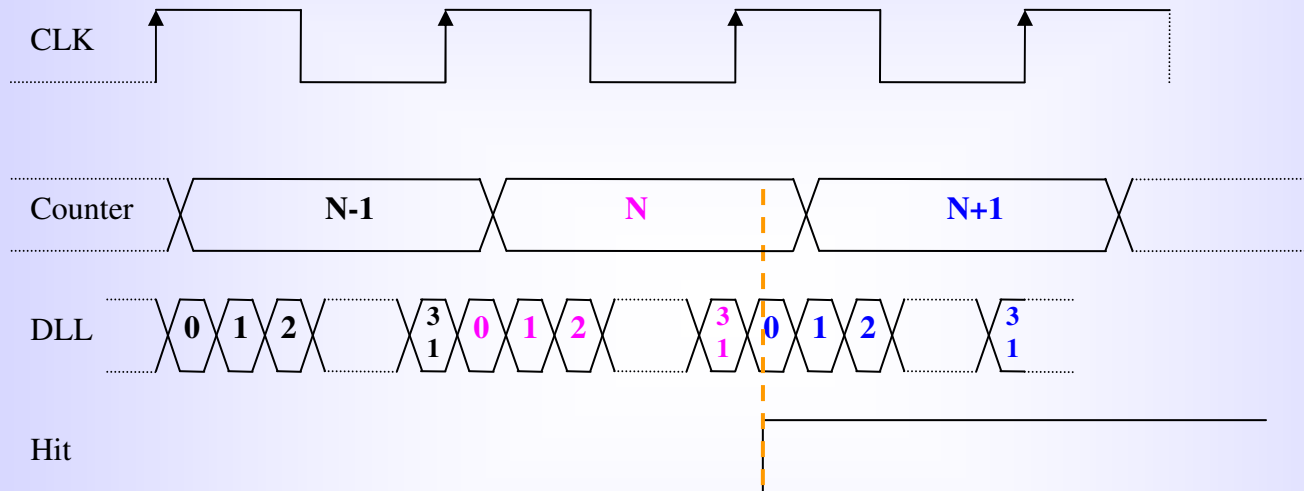
DNL of DLL $< 2\%$ at 27°C



Montecarlo « Process & Mismatch »

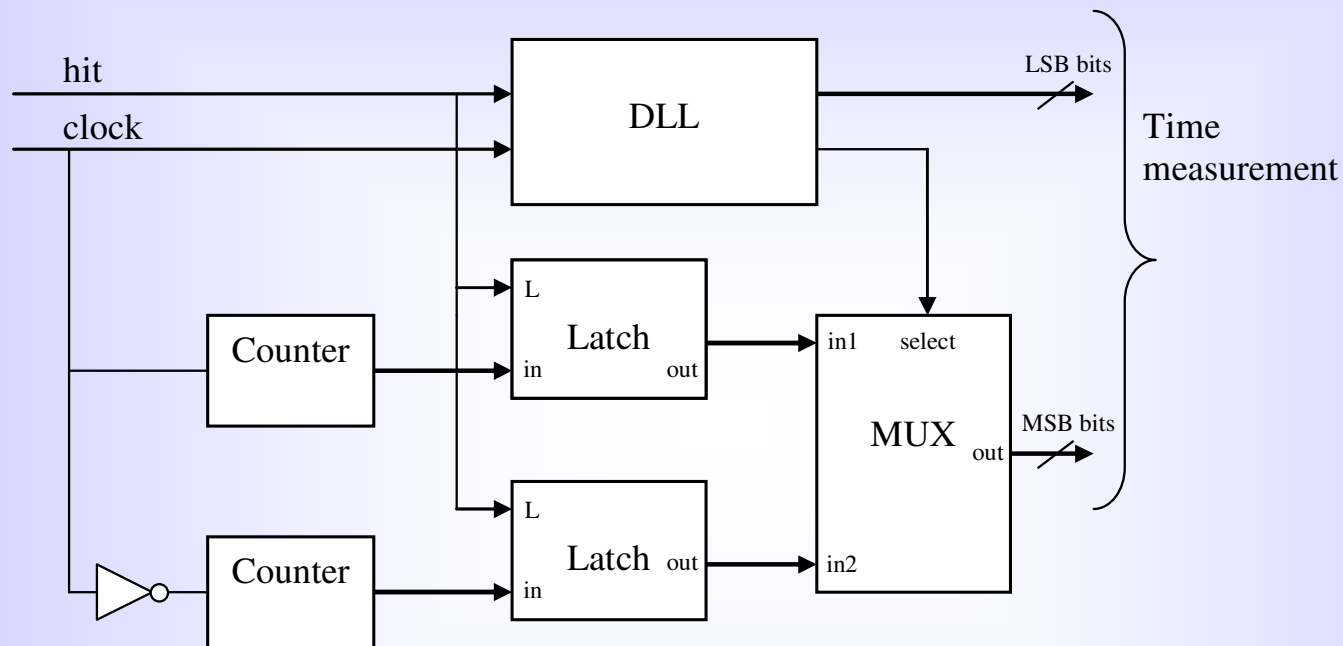


Pb : DLL and counter are synchronous but not in phase!



Code DLL memorized : 0
 Code counter memorized : N instead of N+1 } **Error of one clock period**

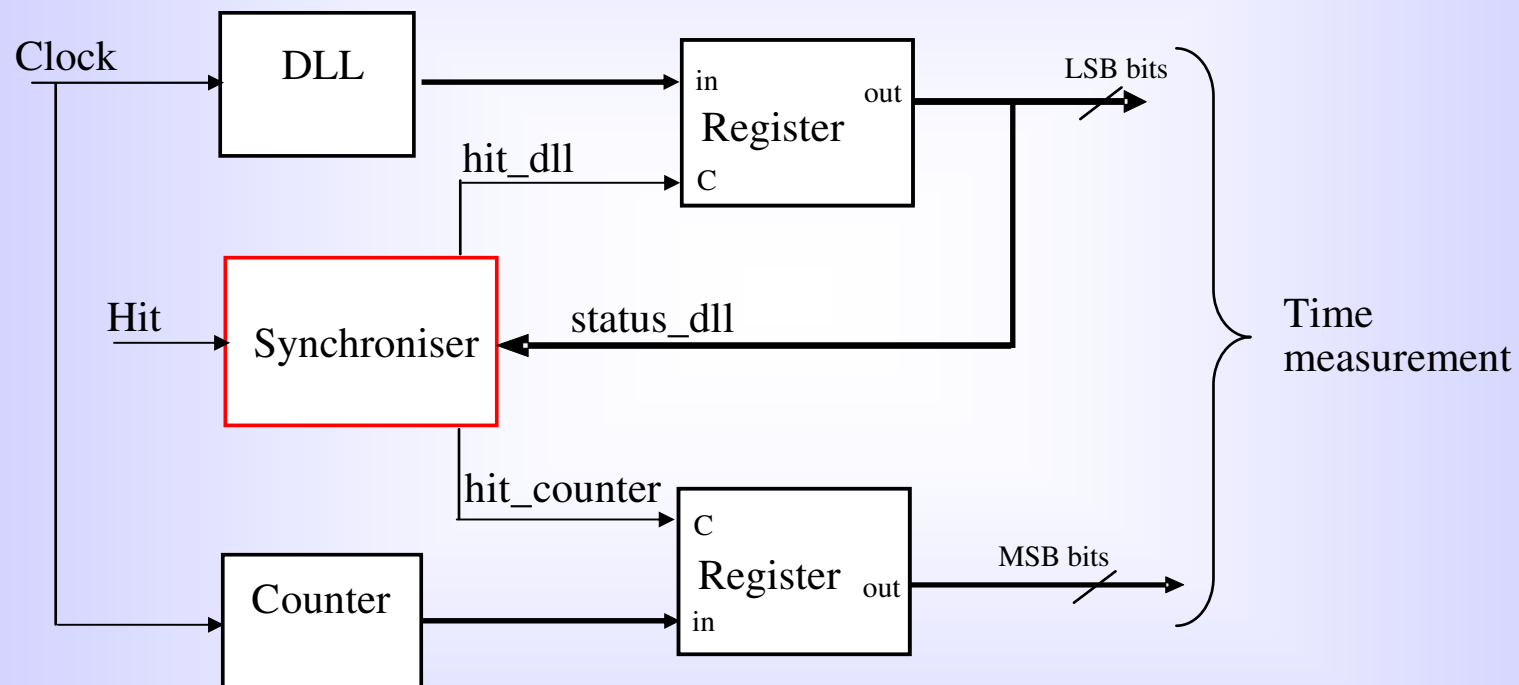
Usually, dual counter structure is used:



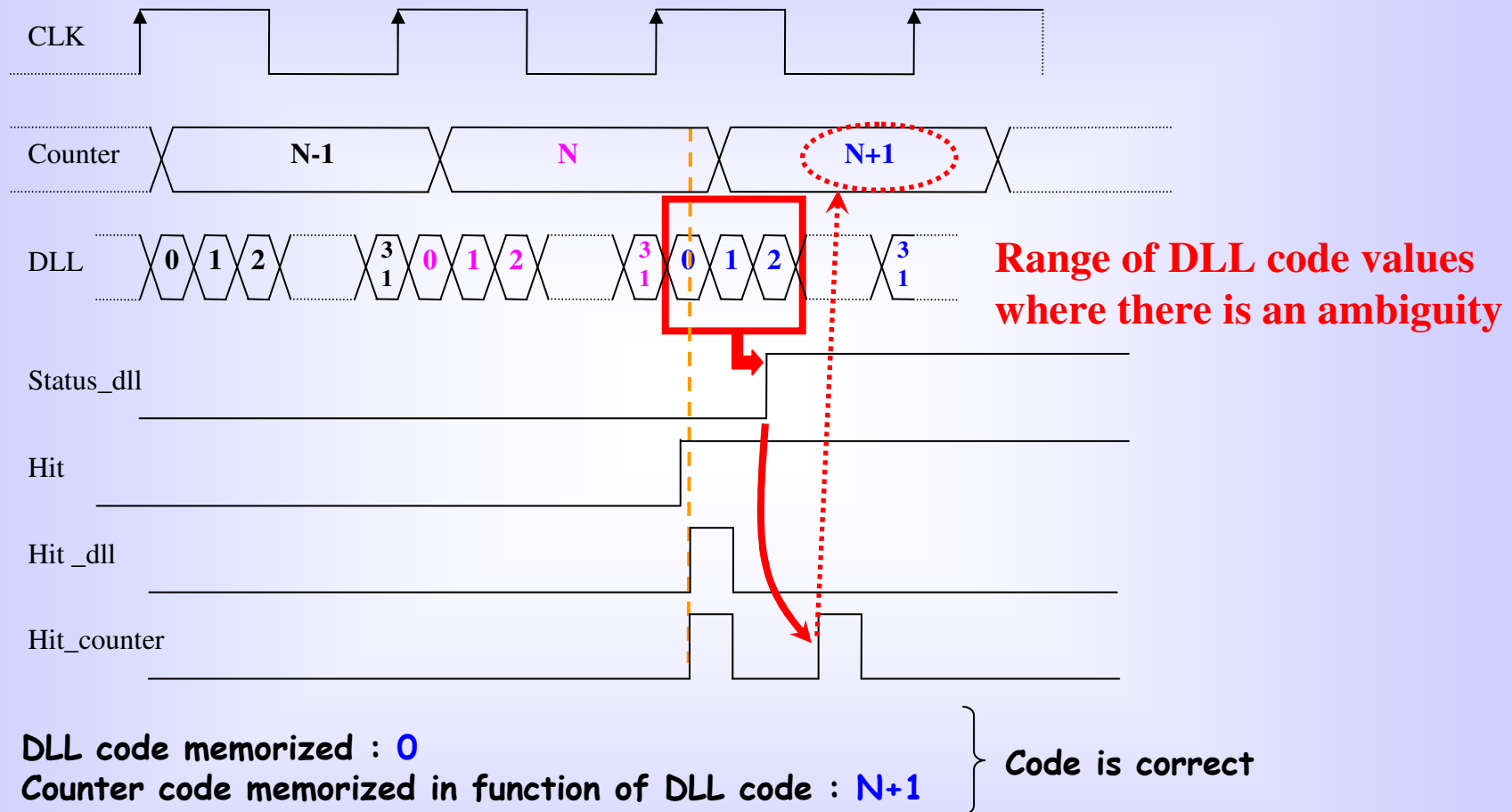
Disadvantages:

- ↗ silicon area (2 counters + multiplexer)
- ↗ power consumption

Principle: production of a 'DLL last cells' flag to delay the counter latch



Event with correction:



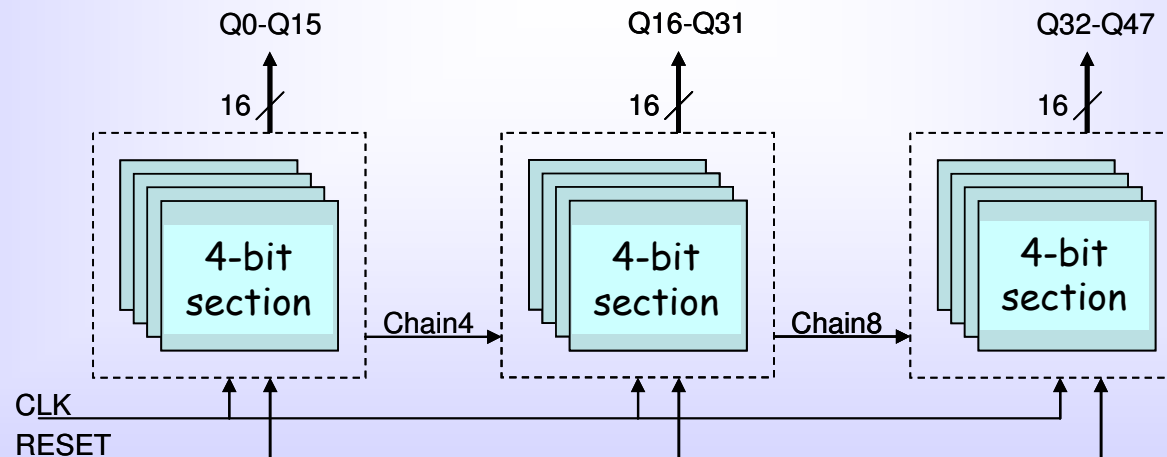
Requirements :

Operating frequency : 160MHz
 Range : 48 bits (20 days)
 Low consumption
 No transient state

} Code Gray

Optimization between complexity / performance:

↪ counter in 3 blocks of 16 bits each consisting of 4 sections of 4 bits

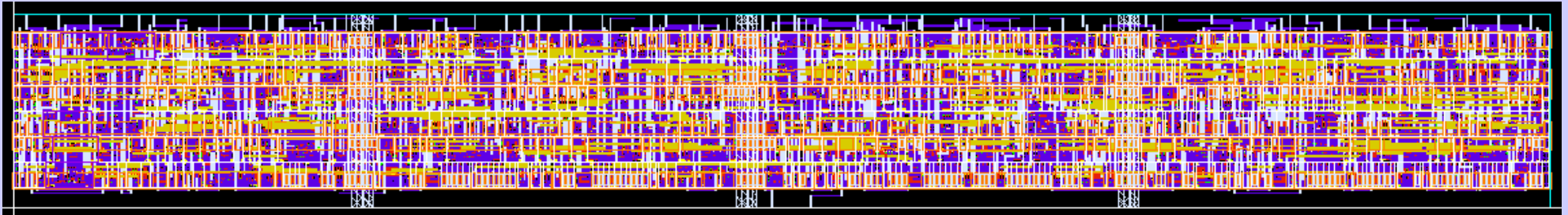


Maximum operating frequency : 200MHz (post layout simulation)

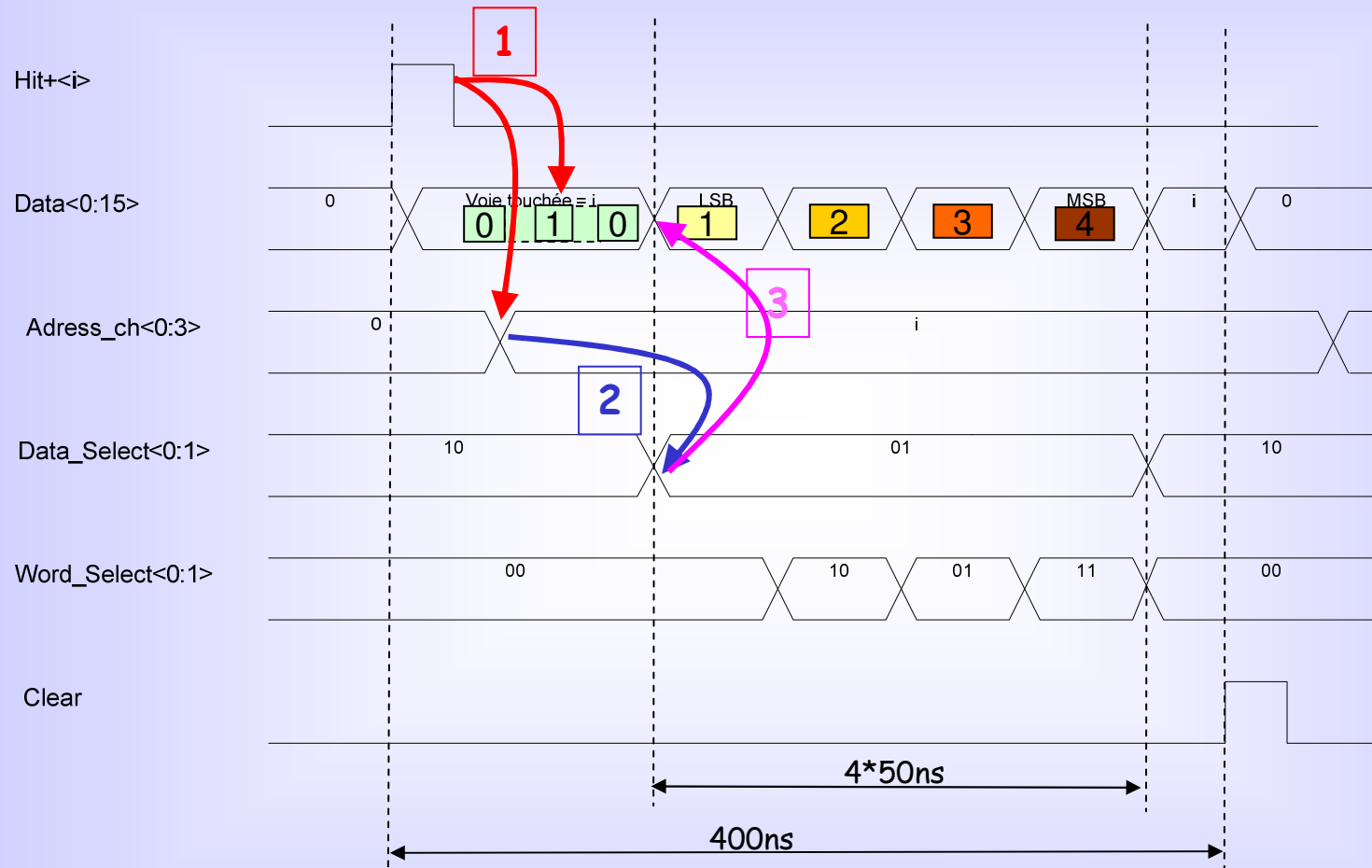
Settling time output < 1.5ns

Size : 780 μ m X 100 μ m

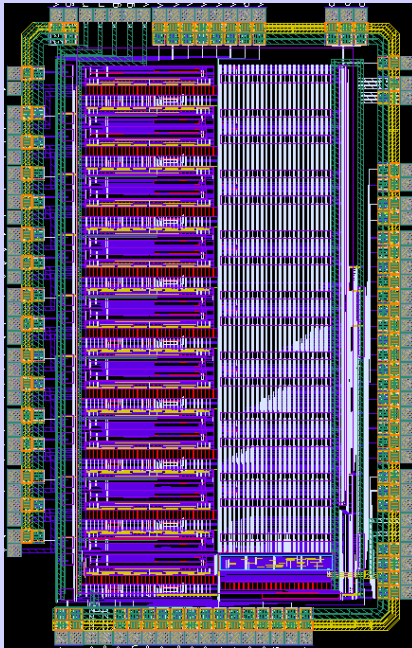
Layout made by Soc Encounter with the help of the IPHC-Strasbourg
(Strasbourg / Abdelkader Himmi)



SNATS : readout sequence



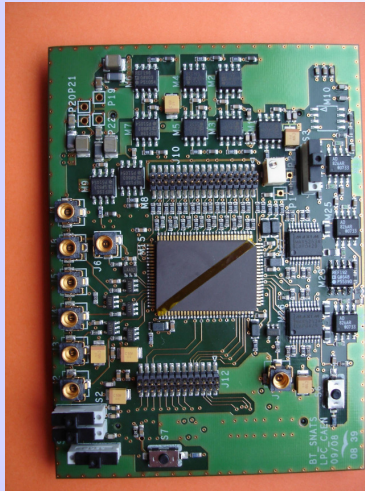
SNATS layout and package



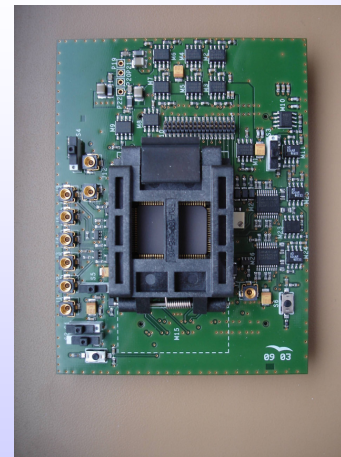
Size : $4467\mu\text{m} \times 2853\mu\text{m}$

Chip area : $\approx 12.7\text{mm}^2$

Package : CQFP100



test-board for
fine tests



test-board for
yield tests

Consumption:

3.3V supply

10mA/DLL + 35mA for the rest

For 8 DLLs: 115 mA $\Rightarrow$ P= 380 mW

Clock signal:

LVDS or single input

Frequency : 160MHz

Low jitter : qq ps RMS

Hit signal :

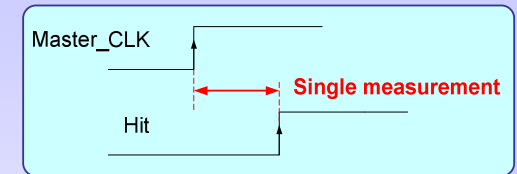
Input level between 1V and 3.3V

Trigger on rising edge

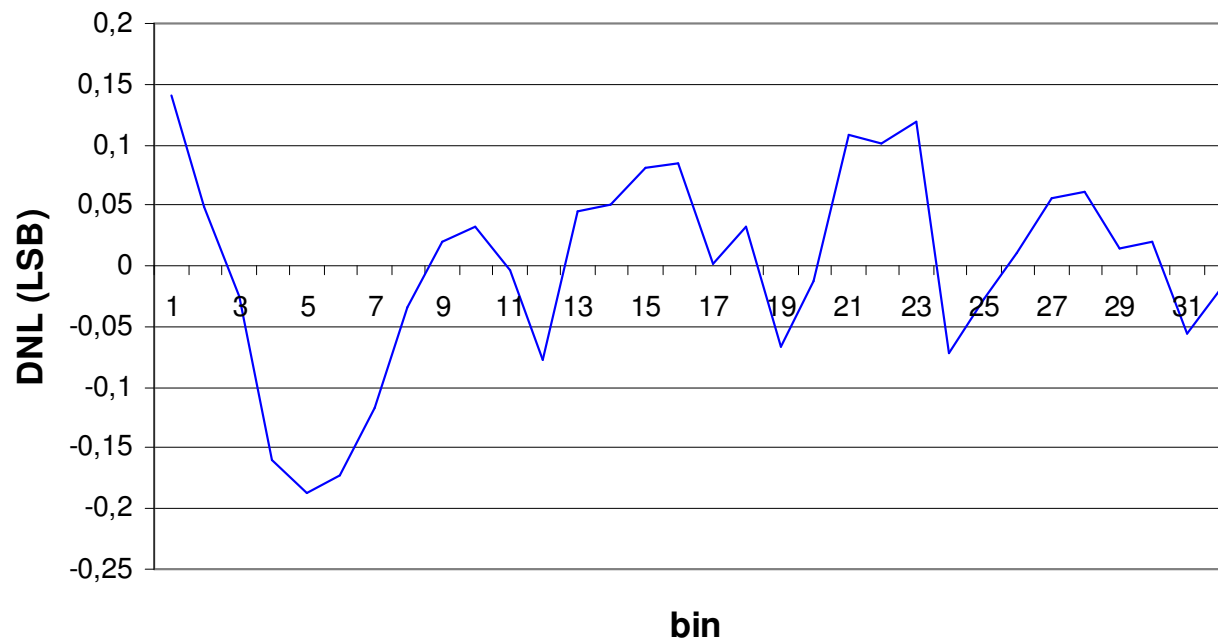
Readout and control signals:

3.3V CMOS Standard

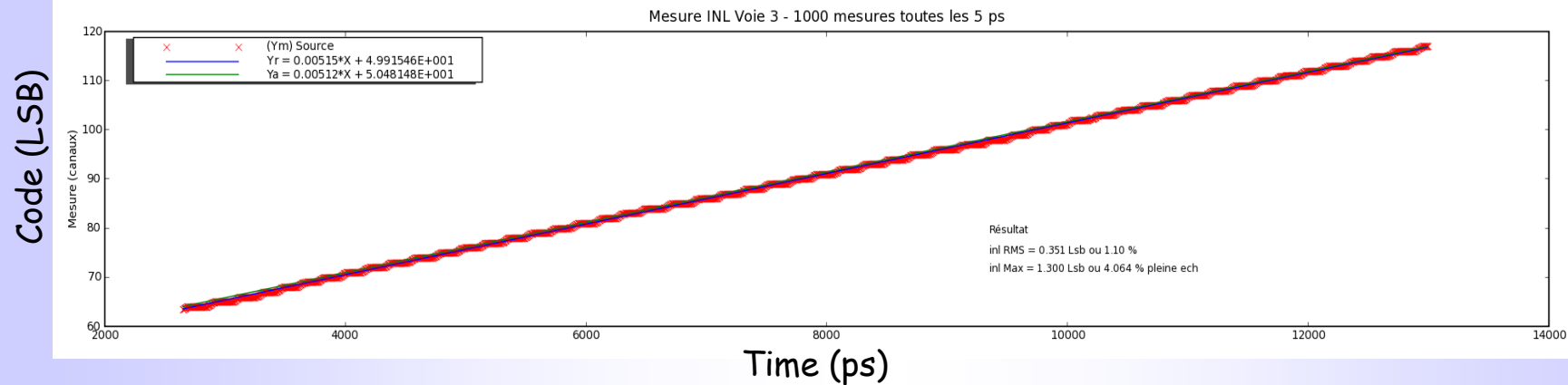
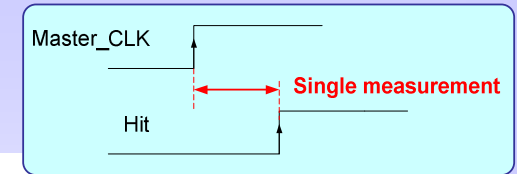
Differential Non Linearity (DNL):



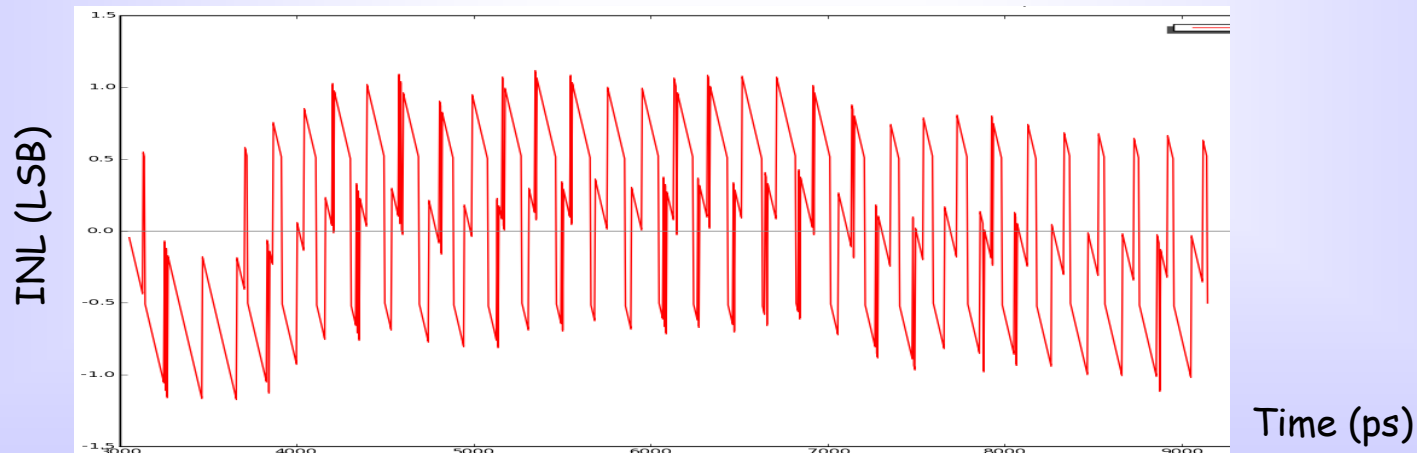
DNL (σ / max): 0.083 / $\pm$ 0.2 LSB



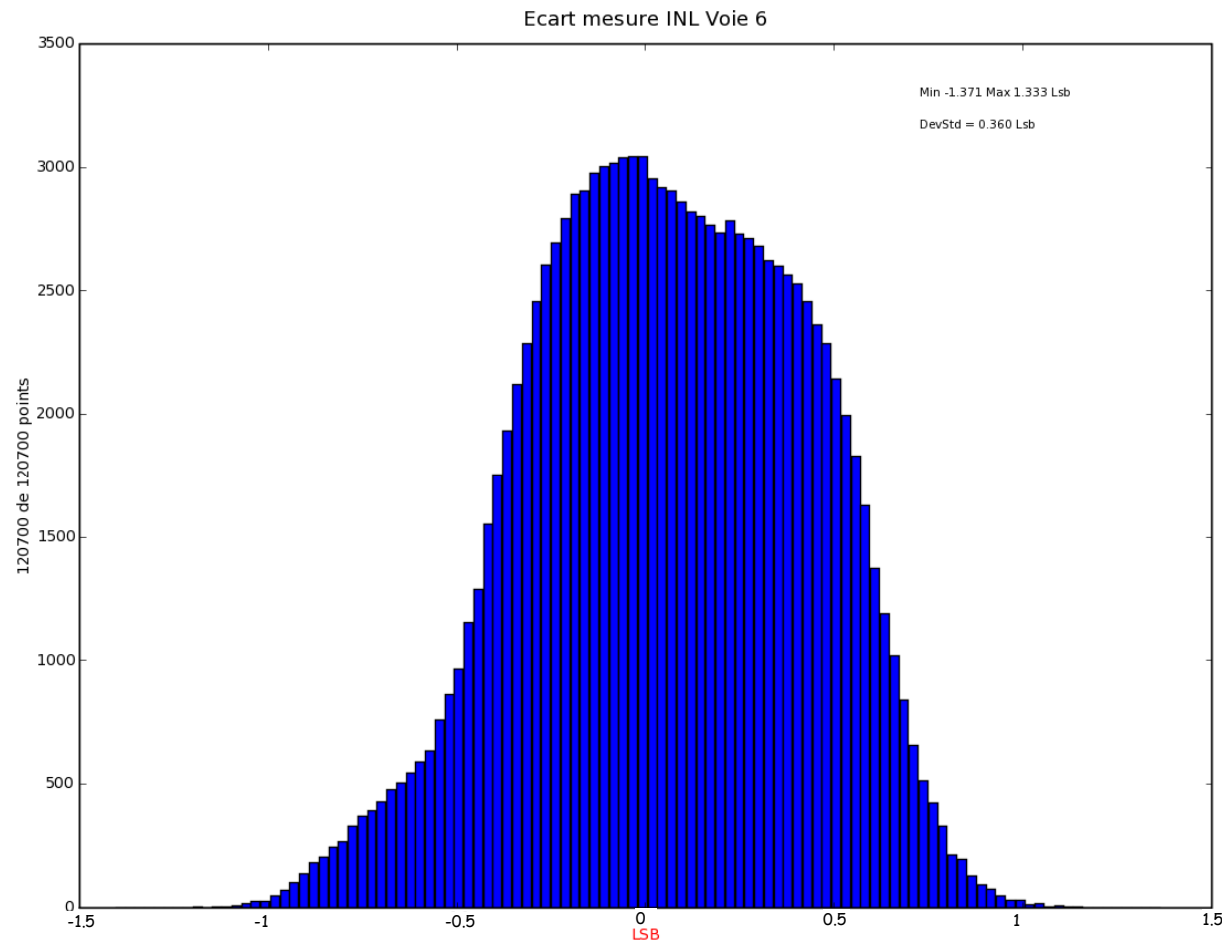
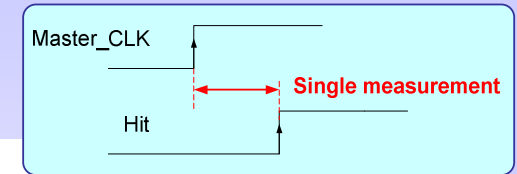
Transfert function:



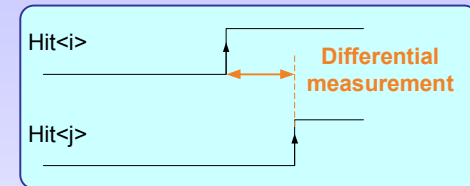
Integral Non Linearity ($\sigma/\max$): 0.083 / ± 0.2 LSB



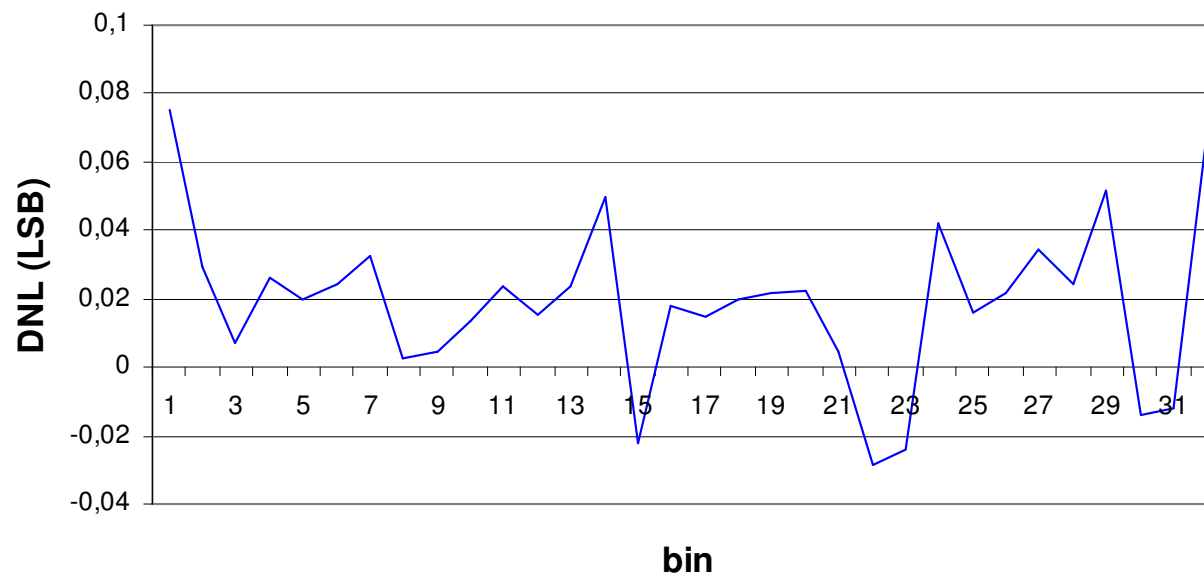
Resolution : $\sigma = 71$ ps



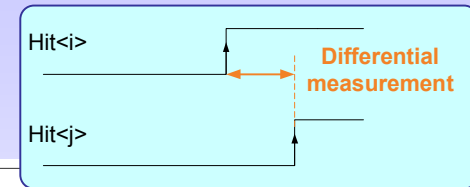
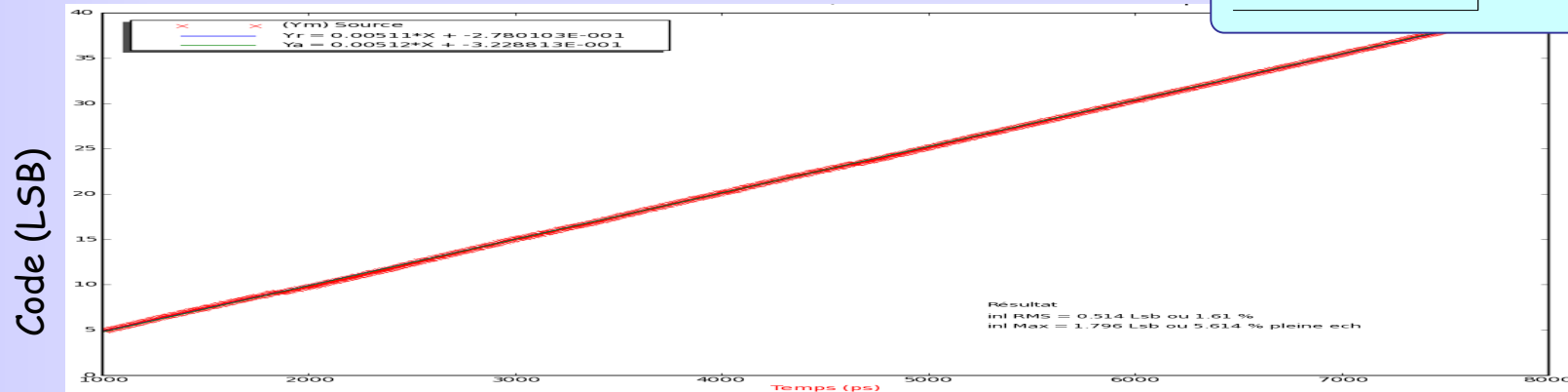
Differential Non Linearity (DNL):



DNL (σ / max): 0.024 / $\pm$ 0.08 LSB

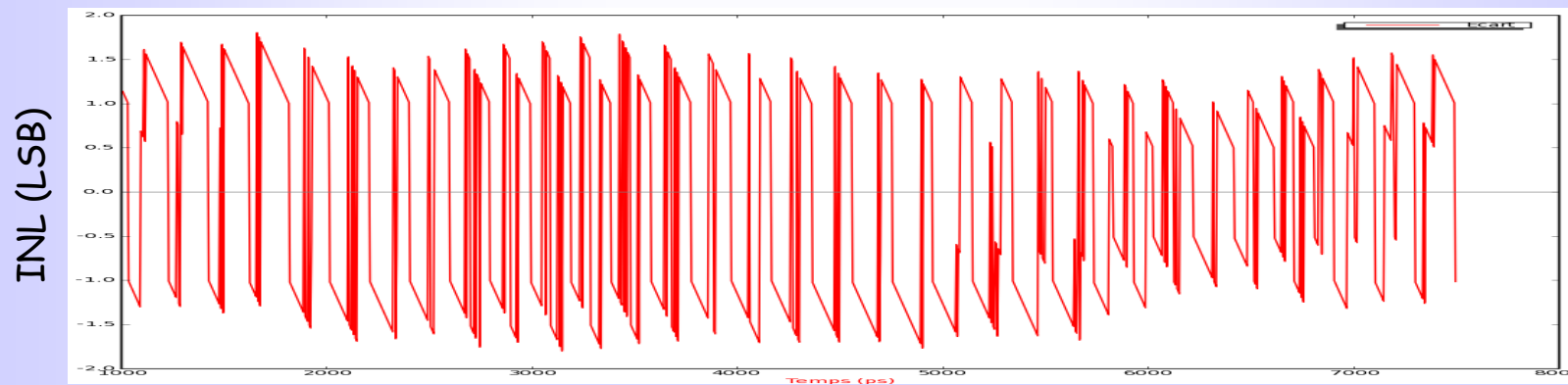


Transfert function:



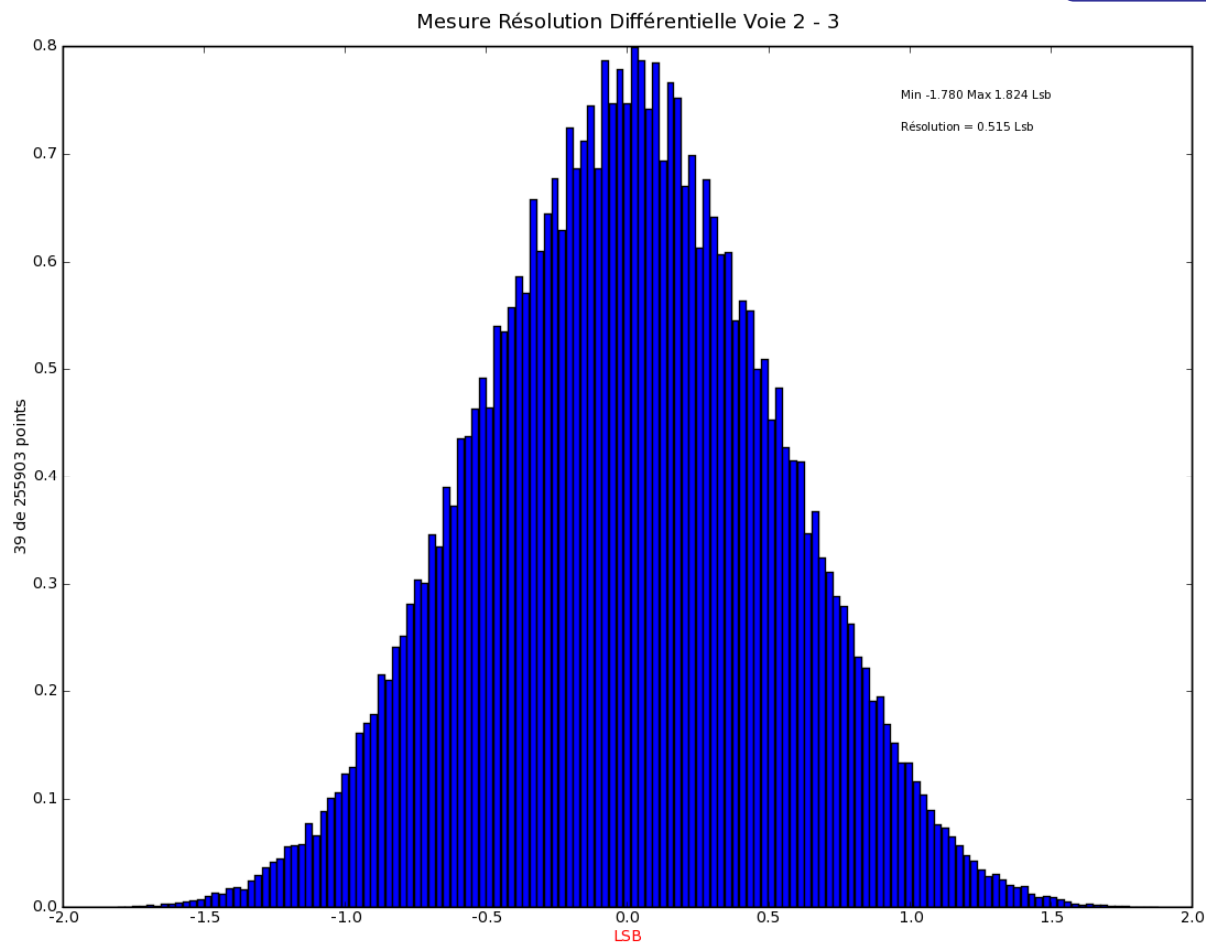
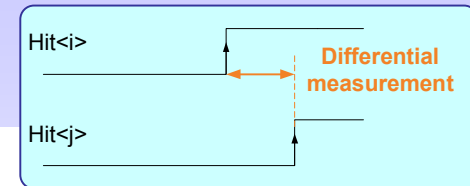
Time interval (ps)

Integral Non Linearity (σ / max): 0.514 / $\pm$ 1.8 LSB



Time interval (ps)

Resolution : $\sigma = 101$ ps



Timing characteristics:

Bin size (LSB)	195.3ps	$\Rightarrow$ Dynamic range ~ 20 days
Clock frequency	160 MHz	
Resolution	Single channel mode 70ps RMS	Differential channel mode 101ps RMS
DNL (σ / max)	0.083 / ± 0.2 LSB	0.024 / ± 0.08 LSB
INL (σ / max)	0.36 / ± 1.3 LSB	0.514 / ± 1.8 LSB
Crosstalk	< ± 1 bin	

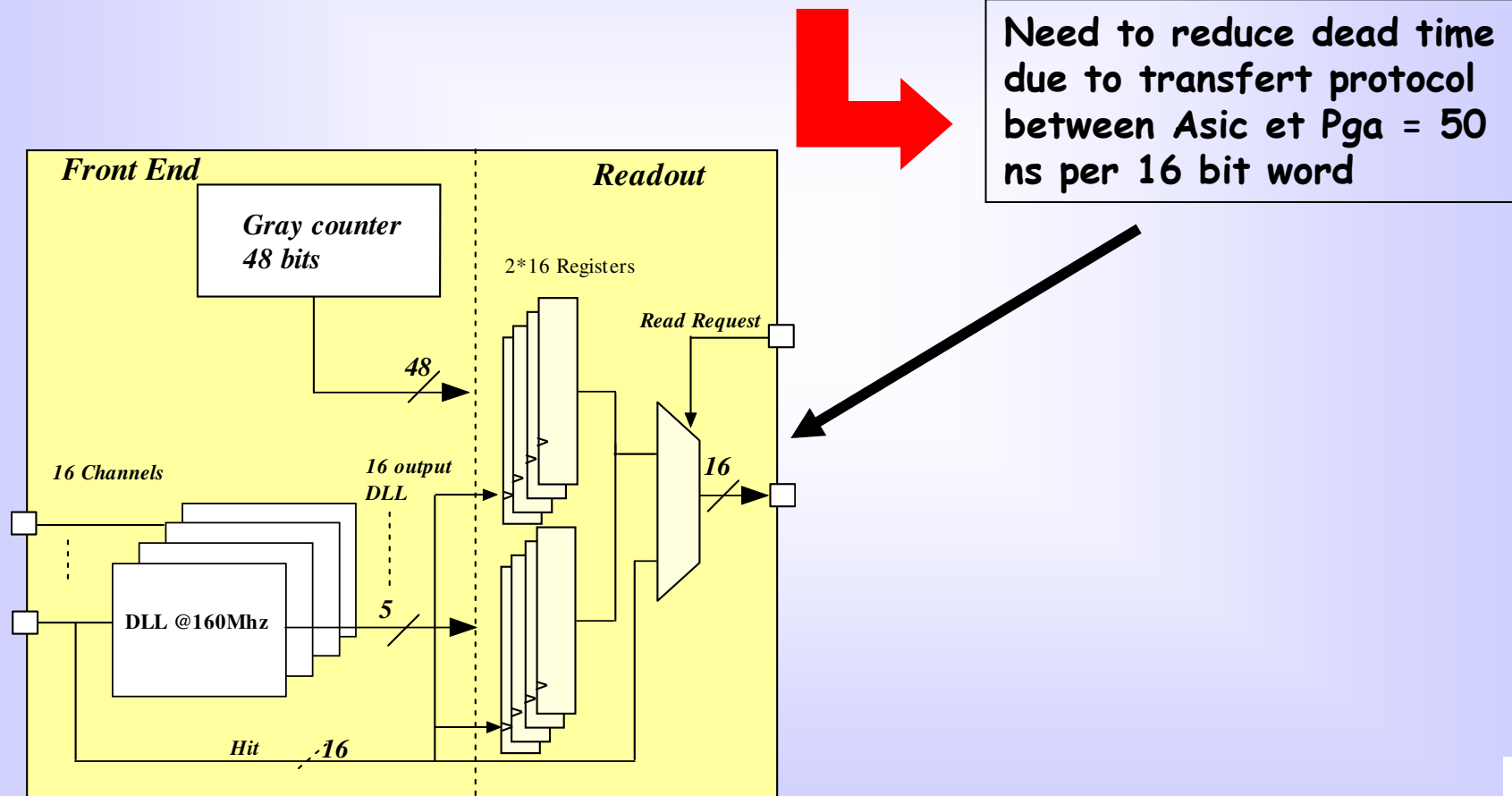


SNATS chip is functional and meets the requirements
for the SuperNEMO calorimeter

DNL for single mode is high and must be improved
 $\rightarrow$ next submission in 2010

Stakes: High counter rate detectors

- INL, DNL, resolution ... : same requirements.
- Increase the Input data rate up to the Mhz per chip per channel.
 - SNATS: 2.5MHz per channel but ~150 kHz per chip



2 options (over many others ...)

▪ Keep almost the same design by just adding a fifo at the output.

↳ increase the input channel rate in burst mode but keep the average readout rate as the previous version.

↳ The fifo size is costly.

▪ Max performance :

➢ Mhz/channel in burst mode but limited by the size of the fifo.

▪ Keep the gray counter inside the Asic with an output variable bus width set by user to reduce the amount of data to be transferred. The gray counter is duplicated inside the associated PGA.

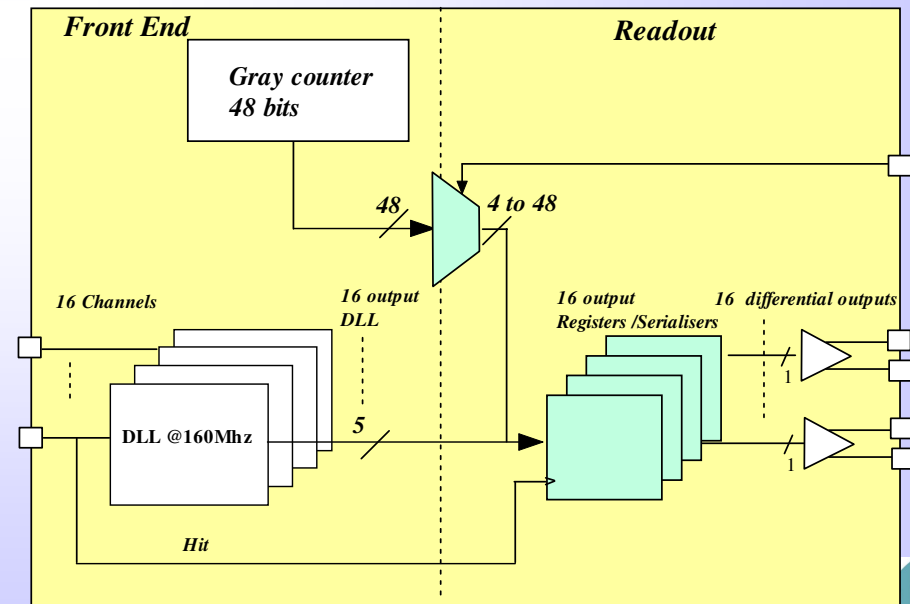
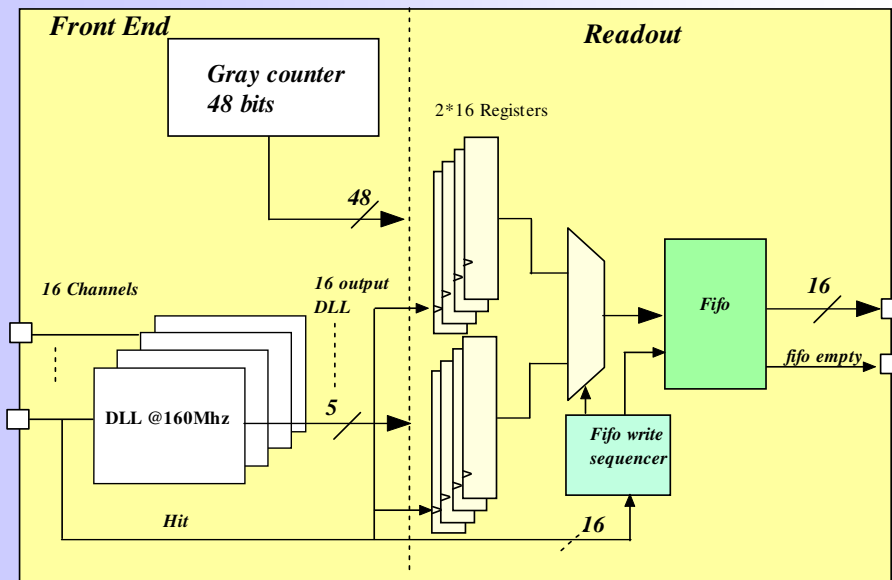
↳ The serial output is synchronous to the clock to ensure the matching between the 2 counters.

↳ 16 differential output channels @ 80 Mhz (160MHz?).

▪ Max performance

➢ 5 DLL bits + 4 gray bits + start bit = 10b @ 80 Mhz = 8Mhz input rate !

➢ Link to performance of the readout acquisition



The end

